

216114US2SDIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF : 21A
3/4/03
M. Prenger

SOICHI INOUE ET AL : GROUP:

SERIAL NO.: NEW APPLICATION : EXAMINER:

FILED: HEREWITH :

FOR: PATTERN FORMING METHOD
AND PATTERN FORMING
APPARATUS

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
Washington, D.C. 20231

SIR:

Prior to examination on the merits, please amend the above-identified patent application as follows:

IN THE SPECIFICATION

Please rewrite the specification as shown below.

Please replace the following paragraph beginning on page 1, line 24, with the following text:

--Consider the case of forming a device pattern by first forming a master mask (a photomask, an X-ray mask, an electron beam mask, an ion beam mask, etc.) for the device pattern using a mask writing tool (which writes a pattern with an electron beam or a laser beam), then radiating the master mask with electromagnetic waves such as light, an X-ray, etc., or with charged particles such as an electron beam, an ion beam, etc. to thereby project